

IN THE CLAIMS

This listing of claims replaces all prior versions and listings of the claims in the above-referenced application.

1. (Currently Amended) A light emitting device comprising:  
a structure comprising:  
a light emitting region disposed between a region of first conductivity type  
and a region of second conductivity type; and  
a distributed Bragg reflector;  
a substrate;  
a first contact electrically connected to the region of first conductivity type; and  
a second contact electrically connected to the region of second conductivity type, the  
second contact comprising a first; and a metal layer having a reflectivity to light emitted by  
the light emitting region greater than 75%, the first metal layer being disposed between the  
substrate and the structure;  
wherein the first contact is electrically connected to the substrate by a second metal  
layer extending along a side surface of the structure  
~~wherein the first and second electrical contacts are formed on a same side of the~~  
~~structure.~~
2. (Currently Amended) The device of claim 1 wherein the light emitting region is disposed between the distributed Bragg reflector and the first metal layer.
3. (Canceled).
4. (Currently Amended) The device of claim 1 wherein the first metal layer comprises a metal selected from the group of Ag, Au, Al, Pt, Pd, Re, Ru, Rh, In, Cr, and alloys thereof.
5. (Original) The device of claim 1 wherein the distributed Bragg reflector has a reflectivity to light emitted by the light emitting region between about 60% and about 90%.
6. (Currently Amended) The device of claim 1 wherein the distributed Bragg reflector and the first metal layer form a resonant cavity, and light generated by the light emitting region is extracted from the resonant cavity through the distributed Bragg reflector.
7. (Currently Amended) The device of claim 1 wherein the distributed Bragg reflector and the first metal layer form a resonant cavity, and a distance between the first

PATENT LAW  
GROUP LLP  
2635 N. FIRST ST.,  
SUITE 225  
SAN JOSE, CA 95131  
(408) 382-0480  
FAX (408) 382-0481

metal layer and the distributed Bragg reflector is an integer multiple of  $\lambda/2$ , where  $\lambda$  is the wavelength of light emitted by the light emitting region in the resonant cavity.

8. (Original) The device of claim 1 wherein the distributed Bragg reflector is disposed between the first contact and the region of first conductivity type.

9. (Original) The device of claim 8 wherein the first contact comprises a ring.

10. (Original) The device of claim 8 wherein the first contact comprises a mesh.

11-15. (Canceled).

16. (Original) The device of claim 1 wherein the first metal layer has a reflectivity to light emitted by the light emitting region greater than 80%.

17. (Original) The device of claim 1 wherein the distributed Bragg reflector has a reflectivity to light emitted by the light emitting region between about 75% and about 85%.

18-24. (Canceled).

PATENT LAW  
GROUP LLP  
2635 N. FIRST ST.  
SUITE 235  
SAN JOSE, CA 95134  
(408) 582-0480  
FAX (408) 382-0481